NSN 5961-01-102-2877

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Inclosure Material:
Metal
Overall Length:
1.125 inches
Overall Diameter:
1.000 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
1.062 inches
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
140.0 off-state voltage, rms total and 200.0 reverse voltage, peak
Current Rating Per Characteristic:
50.00 amperes forward current, total rms megahertz and 2.00 amperes forward current, total rms of standard range
Power Rating Per Characteristic:
5.0 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: pnpn
Test Data Document:
81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:
2 tab, solder lug and 1 threaded stud
Specification Data:
81349-mil-prf-19500 government specification
Shelf Life:
N/α

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Unit Of Measure:

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Mil-std (military Standard):

Mil-prf-19500 spec.